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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Obsolete
Core Processor	HCS12
Core Size	16-Bit
Speed	25MHz
Connectivity	CANbus, I ² C, SCI, SPI
Peripherals	PWM, WDT
Number of I/O	91
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	12K x 8
Voltage - Supply (Vcc/Vdd)	2.35V ~ 5.25V
Data Converters	A/D 16x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	112-LQFP
Supplier Device Package	112-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mc9s12dp256ccpv

1.4 Block Diagram

Figure 1-1 shows a block diagram of the MC9S12DP256B device.

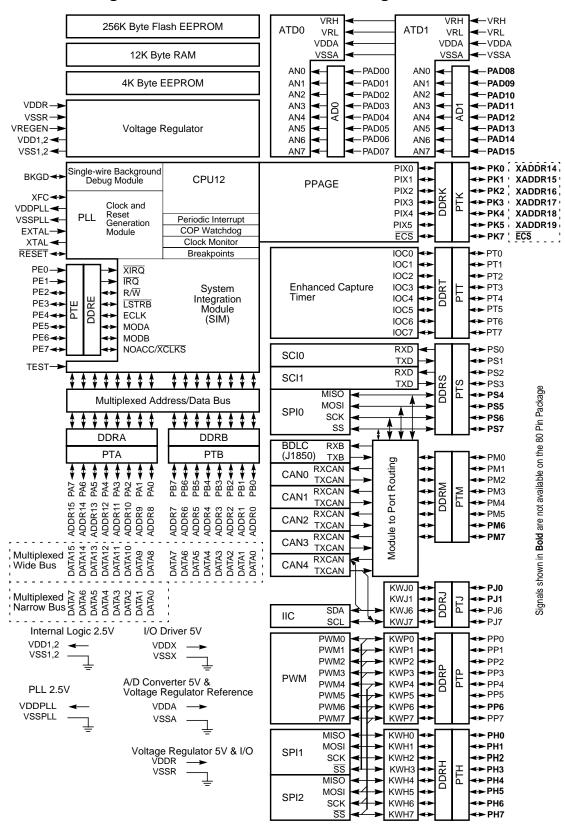


Figure 1-1 MC9S12DP256B Block Diagram

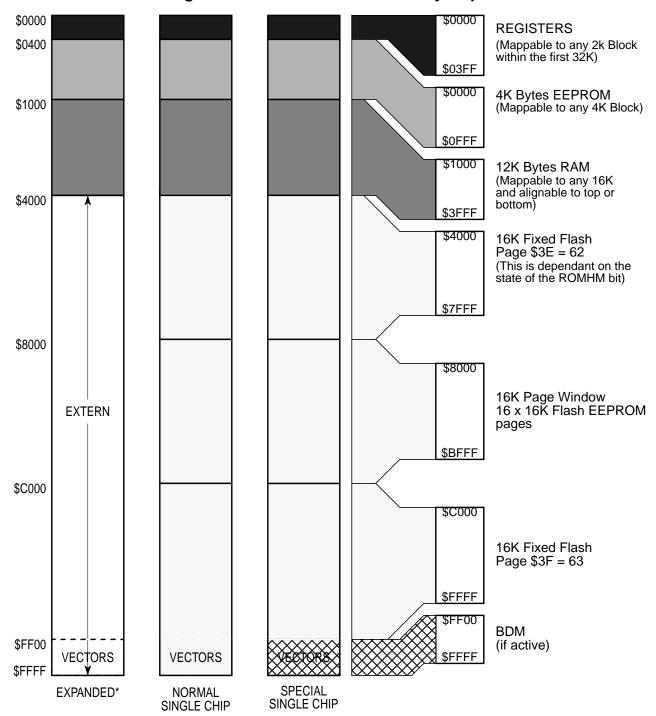


Figure 1-2 MC9S12DP256B Memory Map

^{*} Assuming that a '0' was driven onto port K bit 7 during MCU is reset into normal expanded wide or narrow mode.

\$0028 - \$002F

BKP (Core User Guide)

Address	Name	
\$002D	BKP1X	Rea Writ
\$002E	BKP1H	Rea Writ
\$002F	BKP1L	Rea Writ

	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
ead:	0	0	BK1V5	BK1V4	BK1V3	BK1V2	BK1V1	BK1V0
/rite:			DKTVS	DK1V4	DKTV3	DICTVZ	DKIVI	DKTVU
ead: /rite:	Bit 15	14	13	12	11	10	9	Bit 8
ead: /rite:	Bit 7	6	5	4	3	2	1	Bit 0

\$0030 - \$0031

MMC map 4 of 4 (Core User Guide)

Address	Name
\$0030	PPAGE

Reserved

	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
Read:	0	0	PIX5	PIX4	PIX3	PIX2	PIX1	PIX0
Write:			LIVO	Γ1Λ 1	LIVO	ΓΙΛΖ	FIXI	FIXU
Read:	0	0	0	0	0	0	0	0
Write:								

\$0032 - \$0033

\$0031

MEBI map 3 of 3 (Core User Guide)

Address	Name
\$0032	PORTK
\$0033	DDRK

	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
Read: Write:	Bit 7	6	5	4	3	2	1	Bit 0
Read: Write:	Bit 7	6	5	4	3	2	1	Bit 0

\$0034 - \$003F

CRG (Clock and Reset Generator)

Address	Name
\$0034	SYNR
\$0035	REFDV
\$0036	CTFLG TEST ONLY
\$0037	CRGFLG
\$0038	CRGINT
\$0039	CLKSEL
\$003A	PLLCTL
\$003B	RTICTL
\$003C	COPCTL

	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
Read:	0	0	SYN5	SYN4	SYN3	SYN2	SYN1	SYN0
Write:			STNS	31114	31113	STINZ	STIVI	31110
Read:	0	0	0	0	REFDV3	REFDV2	REFDV1	DEED\/O
Write:					KELD13	KEFUV2	KELDAI	REFDV0
Read:	TOUT7	TOUT6	TOUT5	TOUT4	TOUT3	TOUT2	TOUT1	TOUT0
Write:								
Read:	RTIF	PROF	0	LOCKIF	LOCK	TRACK	SCMIF	SCM
Write:	KIIF	PROF		LUCKIF			SCIVIIF	
Read:	RTIE	0	0	LOCKIE	0	0	SCMIE	0
Write:	KIIE			LOCKIE			SCIVILE	
Read:	PLLSEL	PSTP	SYSWAI	ROAWAI	PLLWAI	CWAI	RTIWAI	COPWAI
Write:	PLLSEL	FSIF	STOWAL	KOAWAI	PLLVVAI	CVVAI	KIIWAI	COPWAI
Read:	CME	PLLON	AUTO	ACQ	0	PRE	PCE	SCME
Write:	CIVIE	PLLON	AUTO	ACQ		FKE	PCE	SCIVIE
Read:	0	DTD6	DTDE	RTR4	RTR3	RTR2	RTR1	DTDO
Write:		RTR6	RTR5	KIK4	KIKS	KIK2	KIKI	RTR0
Read:	WCOD	DCDCK	0	0	0	CDO	CD4	CDO
Write:	WCOP	RSBCK				CR2	CR1	CR0

\$0080 - \$009F

ATD0 (Analog to Digital Converter 10 Bit 8 Channel)

Address	Name		Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
\$0082	ATD0CTL2	Read: Write:	ADPU	AFFC	AWAI	ETRIGLE	ETRIGP	ETRIG	ASCIE	ASCIF
\$0083	ATD0CTL3	Read: Write:	0	S8C	S4C	S2C	S1C	FIFO	FRZ1	FRZ0
\$0084	ATD0CTL4	Read: Write:	SRES8	SMP1	SMP0	PRS4	PRS3	PRS2	PRS1	PRS0
\$0085	ATD0CTL5	Read: Write:	DJM	DSGN	SCAN	MULT	0	СС	СВ	CA
\$0086	ATD0STAT0	Read: Write:	SCF	0	ETORF	FIFOR	0	CC2	CC1	CC0
\$008B	Reserved	Read: Write:	0	0	0	0	0	0	0	0
\$0088	ATD0TEST0	Read: Write:	0	0	0	0	0	0	0	0
\$0089	ATD0TEST1	Read: Write:	0	0	0	0	0	0	0	SC
\$008A	Reserved	Read: Write:	0	0	0	0	0	0	0	0
\$008B	ATD0STAT1	Read: Write:	CCF7	CCF6	CCF5	CCF4	CCF3	CCF2	CCF1	CCF0
\$008C	Reserved	Read: Write:	0	0	0	0	0	0	0	0
\$008D	ATD0DIEN	Read: Write:	Bit 7	6	5	4	3	2	1	Bit 0
\$008E	Reserved	Read: Write:	0	0	0	0	0	0	0	0
\$008F	PORTAD0	Read: Write:	Bit7	6	5	4	3	2	1	BIT 0
\$0090	ATD0DR0H	Read: Write:	Bit15	14	13	12	11	10	9	Bit8
\$0091	ATD0DR0L	Read: Write:	Bit7	Bit6	0	0	0	0	0	0
\$0092	ATD0DR1H	Read: Write:	Bit15	14	13	12	11	10	9	Bit8
\$0093	ATD0DR1L	Read: Write:	Bit7	Bit6	0	0	0	0	0	0
\$0094	ATD0DR2H	Read: Write:	Bit15	14	13	12	11	10	9	Bit8
\$0095	ATD0DR2L	Read: Write:	Bit7	Bit6	0	0	0	0	0	0
\$0096	ATD0DR3H	Read: Write:	Bit15	14	13	12	11	10	9	Bit8
\$0097	ATD0DR3L	Read: Write:	Bit7	Bit6	0	0	0	0	0	0
\$0098	ATD0DR4H	Read: Write:	Bit15	14	13	12	11	10	9	Bit8
\$0099	ATD0DR4L	Read: Write:	Bit7	Bit6	0	0	0	0	0	0
\$009A	ATD0DR5H	Read: Write:	Bit15	14	13	12	11	10	9	Bit8

Freescale Semiconductor, Inc. MC9S12DF256B Device User Guide — V02.14

\$0240 - \$027F

PIM (Port Integration Module PIM_9DP256)

Address	Name		Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
\$0267	PIFH	Read: Write:	PIFH7	PIFH6	PIFH5	PIFH4	PIFH3	PIFH2	PIFH1	PIFH0
\$0268	PTJ	Read: Write:	PTJ7	PTJ6	0	0	0	0	PTJ1	PTJ0
\$0269	PTIJ	Read: Write:	PTIJ7	PTIJ6	0	0	0	0	PTIJ1	PTIJ0
\$026A	DDRJ	Read: Write:	DDRJ7	DDRJ7	0	0	0	0	DDRJ1	DDRJ0
\$026B	RDRJ	Read: Write:	RDRJ7	RDRJ6	0	0	0	0	RDRJ1	RDRJ0
\$026C	PERJ	Read: Write:	PERJ7	PERJ6	0	0	0	0	PERJ1	PERJ0
\$026D	PPSJ	Read: Write:	PPSJ7	PPSJ6	0	0	0	0	PPSJ1	PPSJ0
\$026E	PIEJ	Read: Write:	PIEJ7	PIEJ6	0	0	0	0	PIEJ1	PIEJ0
\$026F	PIFJ	Read: Write:	PIFJ7	PIFJ6	0	0	0	0	PIFJ1	PIFJ0
\$0270 - \$027F	Reserved	Read:								

\$0280 - \$02BF

CAN4 (Motorola Scalable CAN - MSCAN)

Address	Name	[Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
\$0280	CAN4CTL0	Read: Write:	RXFRM	RXACT	CSWAI	SYNCH	TIME	WUPE	SLPRQ	INITRQ
\$0281	CAN4CTL1	Read: Write:	CANE	CLKSRC	LOOPB	LISTEN	0	WUPM	SLPAK	INITAK
\$0282	CAN4BTR0	Read: Write:	SJW1	SJW0	BRP5	BRP4	BRP3	BRP2	BRP1	BRP0
\$0283	CAN4BTR1	Read: Write:	SAMP	TSEG22	TSEG21	TSEG20	TSEG13	TSEG12	TSEG11	TSEG10
\$0284	CAN4RFLG	Read: Write:	WUPIF	CSCIF	RSTAT1	RSTAT0	TSTAT1	TSTAT0	OVRIF	RXF
\$0285	CAN4RIER	Read: Write:	WUPIE	CSCIE	RSTATE1	RSTATE0	TSTATE1	TSTATE0	OVRIE	RXFIE
\$0286	CAN4TFLG	Read: Write:	0	0	0	0	0	TXE2	TXE1	TXE0
\$0287	CAN4TIER	Read: Write:	0	0	0	0	0	TXEIE2	TXEIE1	TXEIE0
\$0288	CAN4TARQ	Read: Write:	0	0	0	0	0	ABTRQ2	ABTRQ1	ABTRQ0
\$0289	CAN4TAAK	Read:	0	0	0	0	0	ABTAK2	ABTAK1	ABTAK0
\$028A	CAN4TBSEL	Write: Read:	0	0	0	0	0	TX2	TX1	TX0
		Write: Read:	0	0	IDAM1	IDAM0	0	IDHIT2	IDHIT1	IDHIT0
\$028B	CAN4IDAC	Write: Read:	0	0	IDAM1 0	0	0	0	0	0
\$028C	Reserved	Write:	J	0	0	0	3	3	0	J

1.7 Part ID Assignments

The part ID is located in two 8-bit registers PARTIDH and PARTIDL (addresses \$001A and \$001B after reset). The read-only value is a unique part ID for each revision of the chip. **Table 1-3** shows the assigned part ID number.

Table 1-3 Assigned Part ID Numbers

Device	Mask Set Number	Part ID ¹
MC9S12DP256	0K79X	\$0010
MC9S12DP256	1K79X	\$0011
MC9S12DP256	2K79X	\$0012

NOTES:

1. The coding is as follows:

Bit 15-12: Major family identifier

Bit 11-8: Minor family identifier

Bit 7-4: Major mask set revision number including FAB transfers

Bit 3-0: Minor - non full - mask set revision

The device memory sizes are located in two 8-bit registers MEMSIZ0 and MEMSIZ1 (addresses \$001C and \$001D after reset). **Table 1-4** shows the read-only values of these registers. Refer to section Module Mapping and Control (MMC) of HCS12 Core User Guide for further details.

Table 1-4 Memory size registers

Register name	Value
MEMSIZ0	\$25
MEMSIZ1	\$81

Pin Name		Pin Name	Pin Name	Pin Name	Power			- Description
Funct. 1	Funct. 2	Funct. 3	Funct. 4	Funct. 5	Supply	CTRL	Reset State	Description
EXTAL	_	_	_	_	VDDPLL	NA	NA	Oscillator Pins
XTAL	_	_	_	_	VDDPLL	NA	NA	Communication in the
RESET	_		_	_	VDDR	None	None	External Reset
TEST	_	_	_	_	N.A.	NA	NA	Test Input
VREGEN	_	_	_	_	VDDX	NA	NA	Voltage Regulator Enable Input
XFC	_	_	_	_	VDDPLL	NA	NA	PLL Loop Filter
BKGD	TAGHI	MODC	_	_	VDDR	Always Up	Up	Background Debug, Tag High, Mode Input
PAD[15]	AN1[7]	ETRIG1	_	_	VDDA	None	None	Port AD Input, Analog Input AN7 of ATD1, External Trigger Input of ATD1
PAD[14:8]	AN1[6:0]	_	_	_	VDDA	None	None	Port AD Inputs, Analog Inputs AN[6:0] of ATD1
PAD[7]	AN0[7]	ETRIG0	_	_	VDDA	None	None	Port AD Input, Analog Input AN7 of ATD0, External Trigger Input of ATD0
PAD[6:0]	AN0[6:0]	_	_	_	VDDA	None	None	Port AD Inputs, Analog Inputs AN[6:0] of ATD0
PA[7:0]	ADDR[15:8]/ DATA[15:8]	_	_	_	VDDR	PUCR	Disabled	Port A I/O, Multiplexed Address/Data
PB[7:0]	ADDR[7:0]/ DATA[7:0]	_	_	_	VDDR	PUCR	Disabled	Port B I/O, Multiplexed Address/Data
PE7	NOACC	XCLKS	_	_	VDDR	PUCR	Up	Port E I/O, Access, Clock Select
PE6	IPIPE1	MODB	_	_	VDDR	pin	RESET is low: own	Port E I/O, Pipe Status, Mode Input
PE5	IPIPE0	MODA	_	_	VDDR	pin	RESET is low: own	Port E I/O, Pipe Status, Mode Input
PE4	ECLK	_	_	_	VDDR	PUCR	Up	Port E I/O, Bus Clock Output
PE3	LSTRB	TAGLO	_	_	VDDR	PUCR	Up	Port E I/O, Byte Strobe, Tag Low
PE2	R/W	_	_	_	VDDR	PUCR	Up	Port E I/O, R/W in expanded modes
PE1	ĪRQ	_	_	_	VDDR	<u> </u>		Port E Input, Maskable Interrupt
PE0	XIRQ	_	_	_	VDDR	- Always up		Port E Input, Non Maskable Interrupt
PH7	KWH7	SS2	_	_	VDDR	PERH/ PPSH Disabled		Port H I/O, Interrupt, SS of SPI2
PH6	KWH6	SCK2	_	_	VDDR	PERH/ PPSH	Disabled	Port H I/O, Interrupt, SCK of SPI2

Table 4-3 Voltage Regulator VREGEN

VREGEN	Description					
1 Internal Voltage Regulator enabled						
0	Internal Voltage Regulator disabled, VDD1,2 and VDDPLL must be supplied externally with 2.5V					

4.3 Security

The device will make available a security feature preventing the unauthorized read and write of the memory contents. This feature allows:

- Protection of the contents of FLASH,
- Protection of the contents of EEPROM,
- Operation in single-chip mode,
- Operation from external memory with internal FLASH and EEPROM disabled.

The user must be reminded that part of the security must lie with the user's code. An extreme example would be user's code that dumps the contents of the internal program. This code would defeat the purpose of security. At the same time the user may also wish to put a back door in the user's program. An example of this is the user downloads a key through the SCI which allows access to a programming routine that updates parameters stored in EEPROM.

4.3.1 Securing the Microcontroller

Once the user has programmed the FLASH and EEPROM (if desired), the part can be secured by programming the security bits located in the FLASH module. These non-volatile bits will keep the part secured through resetting the part and through powering down the part.

The security byte resides in a portion of the Flash array.

Check the Flash Block User Guide for more details on the security configuration.

4.3.2 Operation of the Secured Microcontroller

4.3.2.1 Normal Single Chip Mode

This will be the most common usage of the secured part. Everything will appear the same as if the part was not secured with the exception of BDM operation. The BDM operation will be blocked.

4.3.2.2 Executing from External Memory

The user may wish to execute from external space with a secured microcontroller. This is accomplished by resetting directly into expanded mode. The internal FLASH and EEPROM will be disabled. BDM operations will be blocked.



4.3.3 Unsecuring the Microcontroller

In order to unsecure the microcontroller, the internal FLASH and EEPROM must be erased. This can be done through an external program in expanded mode.

Once the user has erased the FLASH and EEPROM, the part can be reset into special single chip mode. This invokes a program that verifies the erasure of the internal FLASH and EEPROM. Once this program completes, the user can erase and program the FLASH security bits to the unsecured state. This is generally done through the BDM, but the user could also change to expanded mode (by writing the mode bits through the BDM) and jumping to an external program (again through BDM commands). Note that if the part goes through a reset before the security bits are reprogrammed to the unsecure state, the part will be secured again.

4.4 Low Power Modes

The microcontroller features three main low power modes. Consult the respective Block User Guide for information on the module behavior in Stop, Pseudo Stop, and Wait Mode. An important source of information about the clock system is the Clock and Reset Generator User Guide (CRG).

4.4.1 Stop

Executing the CPU STOP instruction stops all clocks and the oscillator thus putting the chip in fully static mode. Wake up from this mode can be done via reset or external interrupts.

4.4.2 Pseudo Stop

This mode is entered by executing the CPU STOP instruction. In this mode the oscillator is still running and the Real Time Interrupt (RTI) or Watchdog (COP) sub module can stay active. Other peripherals are turned off. This mode consumes more current than the full STOP mode, but the wake up time from this mode is significantly shorter.

4.4.3 Wait

This mode is entered by executing the CPU WAI instruction. In this mode the CPU will not execute instructions. The internal CPU signals (address and databus) will be fully static. All peripherals stay active. For further power consumption the peripherals can individually turn off their local clocks.

4.4.4 Run

Although this is not a low power mode, unused peripheral modules should not be enabled in order to save power.

Section 10 Inter-IC Bus (IIC) Block Description

Consult the IIC Block User Guide for information about the Inter-IC Bus module.

Section 11 Serial Communications Interface (SCI) Block Description

There are two Serial Communications Interfaces (SCI1 and SCI0) implemented on the MC9S12DP256B device. Consult the SCI Block User Guide for information about each Serial Communications Interface module.

Section 12 Serial Peripheral Interface (SPI) Block Description

There are three Serial Peripheral Interfaces(SPI2, SPI1 and SPI0) implemented on MC9S12DP256B. Consult the SPI Block User Guide for information about each Serial Peripheral Interface module.

Section 13 J1850 (BDLC) Block Description

Consult the BDLC Block User Guide for information about the J1850 module.

Section 14 Pulse Width Modulator (PWM) Block Description

Consult the PWM 8B8C Block User Guide for information about the Pulse Width Modulator module.

Section 15 Flash EEPROM 256K Block Description

Consult the FTS256K Block User Guide for information about the flash module.

Section 16 EEPROM 4K Block Description

Consult the EETS4K Block User Guide for information about the EEPROM module.

Section 17 RAM Block Description

VSSA C3 VDDA VDD1[□] VSS1 VSS2 C2 VDDR VSSPLL \VDDPLL

Figure 20-1 Recommended PCB Layout 112 LQFP

Figure 20-2 Recommended PCB Layout for 80QFP

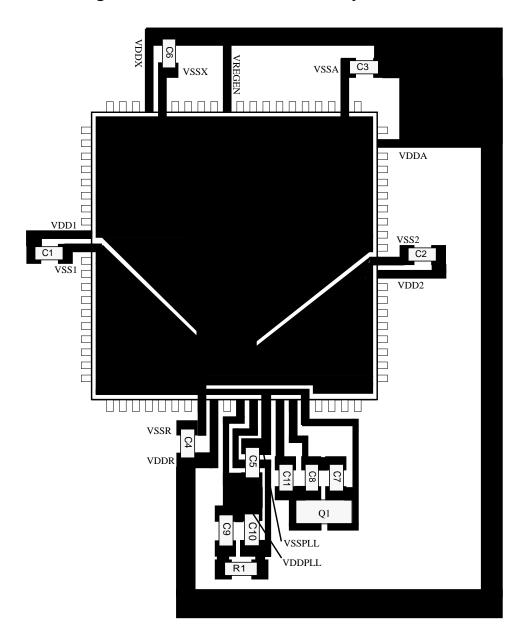


Table A-5 Thermal Package Characteristics¹

Num	С	Rating	Symbol	Min	Тур	Max	Unit
1	Т	Thermal Resistance LQFP112, single sided PCB ²	θ_{JA}	-	-	54	°C/W
2	Т	Thermal Resistance LQFP112, double sided PCB with 2 internal planes ³	θ_{JA}	-	-	41	°C/W
3	Т	Thermal Resistance LQFP 80, single sided PCB	θ_{JA}	-	-	51	°C/W
4	Т	Thermal Resistance LQFP 80, double sided PCB with 2 internal planes	θ_{JA}	-	-	41	°C/W

NOTES:

- 1. The values for thermal resistance are achieved by package simulations
- 2. PC Board according to EIA/JEDEC Standard 51-2
- 3. PC Board according to EIA/JEDEC Standard 51-7

A.1.9 I/O Characteristics

This section describes the characteristics of all 5V I/O pins. All parameters are not always applicable, e.g. not all pins feature pull up/down resistances.

Table A-6 5V I/O Characteristics

С	Rating	Symbol	Min	Тур	Max	Unit
Р	Input High Voltage	V _{IH}	0.65*V _{DD5}	-	-	V
Т	Input High Voltage	V _{IH}	-	-	VDD5 + 0.3	V
Р	Input Low Voltage	V _{IL}	-	-	0.35*V _{DD5}	V
Т	Input Low Voltage	V _{IL}	VSS5 - 0.3	-	-	V
С	Input Hysteresis	V _{HYS}		250		mV
Р	Input Leakage Current (pins in high impedance input mode) ¹ $V_{in} = V_{DD5}$ or V_{SS5}	I _{in}	-2.5	-	2.5	μΑ
Р	Output High Voltage (pins in output mode) Partial Drive $I_{OH} = -2mA$ Full Drive $I_{OH} = -10mA$	V _{OH}	V _{DD5} – 0.8	-	-	V
Р	Output Low Voltage (pins in output mode) Partial Drive I _{OL} = +2mA Full Drive I _{OL} = +10mA	V _{OL}	-	-	0.8	V
Р	Internal Pull Up Device Current, tested at V _{IL} Max.	I _{PUL}	-	-	-130	μΑ
Р	Internal Pull Up Device Current, tested at V _{IH} Min.	I _{PUH}	-10	-	-	μΑ
Р	Internal Pull Down Device Current, tested at V _{IH} Min.	I _{PDH}	-	-	130	μΑ
Р	Internal Pull Down Device Current, tested at V _{IL} Max.	I _{PDL}	10	-	-	μΑ
D	Input Capacitance	C _{in}		6	-	pF
Т	Injection current ² Single Pin limit Total Device Limit. Sum of all injected currents	I _{ICS} I _{ICP}	-2.5 -25	-	2.5 25	mA
Р	Port H, J, P Interrupt Input Pulse filtered ³	t _{PULSE}			3	μs
Р	Port H, J, P Interrupt Input Pulse passed ³	t _{PULSE}	10			μs
	P T P T C P P P P P P P P P P P D T P	P Input High Voltage T Input High Voltage P Input Low Voltage T Input Low Voltage C Input Hysteresis Input Leakage Current (pins in high impedance input mode)¹ V _{in} = V _{DD5} or V _{SS5} Output High Voltage (pins in output mode) Partial Drive I _{OH} = -2mA Full Drive I _{OH} = -10mA Output Low Voltage (pins in output mode) Partial Drive I _{OL} = +2mA Full Drive I _{OL} = +10mA P Internal Pull Up Device Current, tested at V _{IL} Max. P Internal Pull Up Device Current, tested at V _{IH} Min. P Internal Pull Down Device Current, tested at V _{IH} Min. P Internal Pull Down Device Current, tested at V _{IL} Max. D Input Capacitance T Injection current² Single Pin limit Total Device Limit. Sum of all injected currents P Port H, J, P Interrupt Input Pulse filtered³	P Input High Voltage V IH T Input High Voltage V IL T Input Low Voltage V IL T Input Low Voltage V IL T Input Leakage Current (pins in high impedance input mode)¹ Vin = VDDs or VSSS D Output High Voltage (pins in output mode) Partial Drive IOH = -2mA Full Drive IOH = -10mA Output Low Voltage (pins in output mode) Partial Drive IOL = +2mA Full Drive IOL = +10mA P Internal Pull Up Device Current, tested at VIH Min. P Internal Pull Up Device Current, tested at VIH Min. P Internal Pull Down Device Current, tested at VIH Min. P Internal Pull Down Device Current, tested at VIH Min. I Internal Pull Down Device Current, tested at VIH Min. I Internal Pull Down Device Current, tested at VIH Min. I Internal Pull Down Device Current, tested at VIH Min. I Internal Pull Down Device Current, tested at VIH Min. I Internal Pull Down Device Current, tested at VIH Min. I Internal Pull Down Device Current, tested at VIH Min. I Internal Pull Down Device Current, Injection current² Single Pin limit Total Device Limit. Sum of all injected currents I PULSE P Port H, J, P Interrupt Input Pulse filtered³ I PULSE	P Input High Voltage T Input High Voltage VIH P Input Low Voltage VIL T Input Low Voltage VIL T Input Low Voltage VIL VSS5 - 0.3 C Input Hysteresis VHYS Input Leakage Current (pins in high impedance input mode) VIL VSS5 - 0.3 VOHUT High Voltage (pins in output mode) Partial Drive IoH = -2mA Full Drive IoH = -10mA Output Low Voltage (pins in output mode) Partial Drive IoL = +2mA Full Drive IoL = +10mA P Internal Pull Up Device Current, tested at VIL Max. P Internal Pull Up Device Current, tested at VIH Min. P Internal Pull Down Device Current, tested at VIH Min. P Internal Pull Down Device Current, tested at VIL Max. P Internal Pull Down Device Current, tested at VIL Min. P Internal Pull Down Device Current, tested at VIL Min. P Internal Pull Down Device Current, tested at VIL Min. I Input Capacitance T Injection current² Single Pin limit Total Device Limit. Sum of all injected currents I PULSE Tepulse Tepulse	Input High Voltage	P Input High Voltage

NOTES:

- 1. Maximum leakage current occurs at maximum operating temperature. Current decreases by approximately one-half for each 8 C to 12 C in the temperature range from 50 C to 125 C.
- 2. Refer to Section A.1.4 Current Injection, for more details
- 3. Parameter only applies in STOP or Pseudo STOP mode.



A.3.1.3 Sector Erase

Erasing a 512 byte Flash sector or a 4 byte EEPROM sector takes:

$$t_{era} \approx 4000 \cdot \frac{1}{f_{NVMOP}}$$

The setup time can be ignored for this operation.

A.3.1.4 Mass Erase

Erasing a NVM block takes:

$$t_{mass} \approx 20000 \cdot \frac{1}{f_{NVMOP}}$$

The setup time can be ignored for this operation.

A.3.1.5 Blank Check

The time it takes to perform a blank check on the Flash or EEPROM is dependant on the location of the first non-blank word starting at relative address zero. It takes one bus cycle per word to verify plus a setup of the command.

$$t_{check} \approx location \cdot t_{cyc} + 10 \cdot t_{cyc}$$

Table A-11 NVM Timing Characteristics

Condit	Conditions are shown in Table A-4 unless otherwise noted								
Num	С	Rating	Symbol	Min	Тур	Max	Unit		
1	D	External Oscillator Clock	f _{NVMOSC}	0.5		50 ¹	MHz		
2	D	Bus frequency for Programming or Erase Operations	f _{NVMBUS}	1			MHz		
3	D	Operating Frequency	f _{NVMOP}	150		200	kHz		
4	Р	Single Word Programming Time	t _{swpgm}	46 ²		74.5 ³	μs		
5	D	Flash Burst Programming consecutive word ⁴	t _{bwpgm}	20.4 ²		31 ³	μs		
6	D	Flash Burst Programming Time for 32 Words ⁴	t _{brpgm}	678.4 ²		1035.5 ³	μs		
7	Р	Sector Erase Time	t _{era}	20 ⁵		26.7 ³	ms		
8	Р	Mass Erase Time	t _{mass}	100 ⁵		133 ³	ms		
9	D	Blank Check Time Flash per block	t _{check}	11 ⁶		32778 ⁷	t _{cyc}		
10	D	Blank Check Time EEPROM per block	t _{check}	11 ⁶		2058 ⁷	t _{cyc}		

NOTES:

- 1. Restrictions for oscillator in crystal mode apply!
- 2. Minimum Programming times are achieved under maximum NVM operating frequency f_{NVMOP} and maximum bus frequency f_{bus}.



A.4 Voltage Regulator

The on-chip voltage regulator is intended to supply the internal logic and oscillator circuits. No external DC load is allowed.

Table A-13 Voltage Regulator Recommended Load Capacitances

Rating	Symbol	Min	Тур	Max	Unit
Load Capacitance on VDD1, 2	C _{LVDD}		220		nF
Load Capacitance on VDDPLL	C _{LVDDfcPLL}		220		nF

A.7.2 Slave Mode

Figure A-7 and Figure A-8 illustrate the slave mode timing. Timing values are shown in Table A-19.

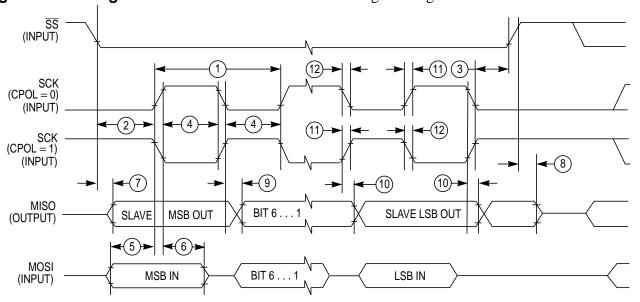


Figure A-7 SPI Slave Timing (CPHA = 0)

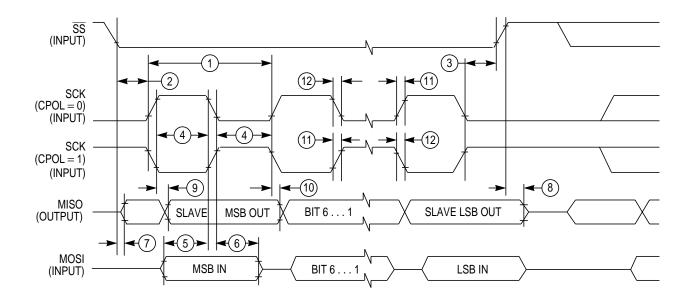


Figure A-8 SPI Slave Timing (CPHA =1)